



# LAPD-3-09-17-CHIP

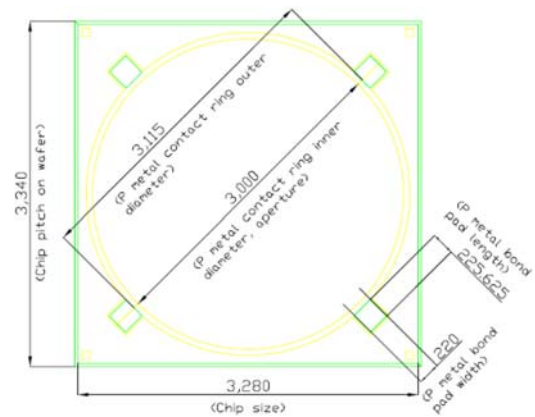


## TECHNICAL DATA

### Photodiode Chip die

### InGaAs

LAPD-3-09-17-CHIP adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The active area is  $\varnothing$  3 mm respectively.



### Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	$U_R$	20	V
Reverse Current	$I_R$	20	mA
Forward current	$I_F$	10	mA
Operating Temperature	$T_{opr}$	-20 ... +85	°C
Storage Temperature	$T_{stg}$	-40 ... +85	°C

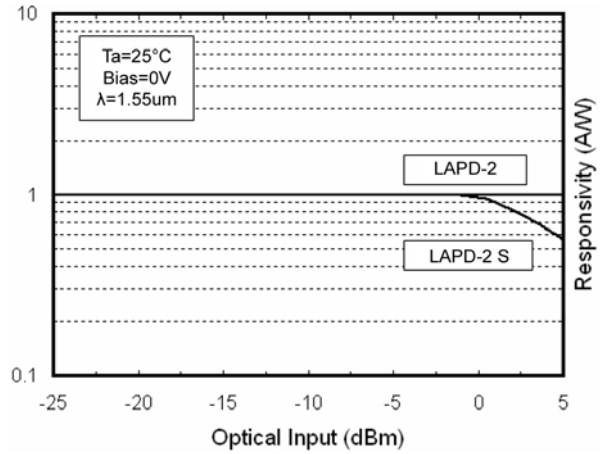
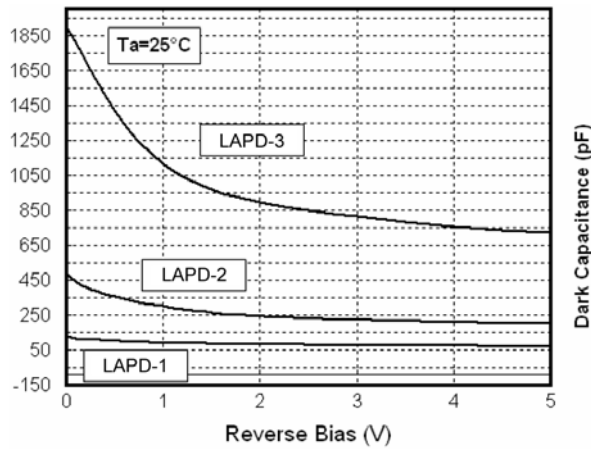
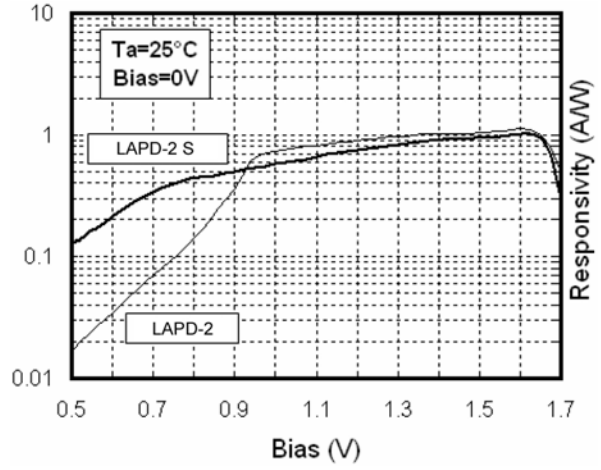
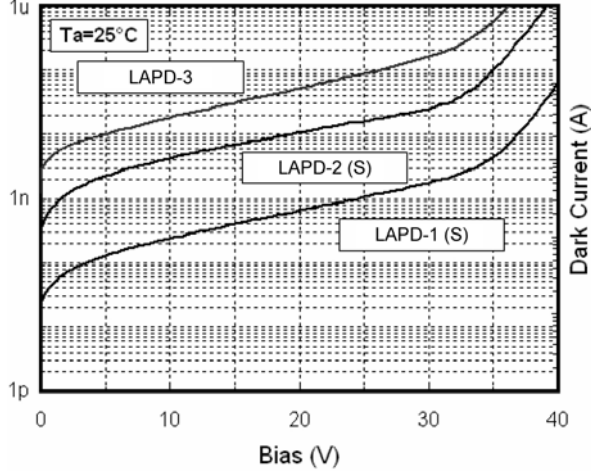
### Specifications

Item	Min.	Typ.	Max.	Unit
Wavelength Range	0.9 .. 1.7			$\mu$ m
Active Area	$\varnothing$ 3			mm
Saturation Power	1550 nm	-	2	dBm
Specific Detectivity ( $D^*$ )	1550 nm	2.5	5	$10^{12}$ Jones
Responsibility (0 V)	650 nm	0.02	0.05	A/W
	850 nm	0.10	0.20	
	1310 nm	0.80	0.90	
	1550 nm	0.85	0.95	
Capacitance	0 V	-	1800	pF
	-5 V	-	700	
Dark Current	-5 V	-	25	nA
Shunt Resistance	2	10	-	M $\Omega$
Chip Size	3280 x 3280			$\mu$ m
Chip Thickness	300			$\mu$ m

**Packing:** Chips on adhesive film



**Typical Performance Curves**



LAPD-2 Spatial Response  
 Ta=25°C, Bias=0V,  $\lambda=1550\text{nm}$

